High-Power Industrial Transistors

NPN silicon power transistor designed for applications in industrial and commercial equipment including high fidelity audio amplifiers, series and shunt regulators and power switches.

Features

- Collector Emitter Sustaining Voltage V_{CEO(sus)} = 140 Vdc (Min)
- Excellent Second Breakdown Capability
- Pb-Free Package is Available*

MAXIMUM RATINGS (Note 1)

. ,			
Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	140	Vdc
Collector-Base Voltage	V _{CB}	160	Vdc
Emitter-Base Voltage	V _{EB}	7.0	Vdc
Collector Current - Continuous - Peak	I _C	10 15	Adc
Base Current – Continuous – Peak	Ι _Β	7.0 -	Adc
Total Device Dissipation @ T _C = 25°C Derate above 25°C (Note 2)	P _D	117 0.67	W W/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-65 to +200	°C

THERMAL CHARACTERISTICS

Characteristics	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	R _{e.IC}	1.17	°C/W

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

- 1. Indicates JEDEC Registered Data.
- 2. This data guaranteed in addition to JEDEC registered data.



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10 AMPERE POWER TRANSISTOR NPN SILICON 140 VOLTS – 117 WATTS



TO-204AA (TO-3) CASE 1-07 STYLE 1

MARKING DIAGRAM



2N3442 = Device Code
G = Pb-Free Package
A = Assembly Location

Y = Year WW = Work Week MEX = Country of Origin

ORDERING INFORMATION

Device	Package	Shipping
2N3442	TO-204	100 Units / Tray
2N3442G	TO-204 (Pb-Free)	100 Units / Tray

^{*}For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector–Emitter Sustaining Voltage (I _C = 200 mAdc, I _B = 0)	V _{CEO(sus)}	140	_	Vdc
Collector Cutoff Current (V _{CE} = 140 Vdc, I _B = 0)	ICEO	-	200	mAdc
Collector Cutoff Current $(V_{CE} = 140 \text{ Vdc}, V_{BE(off)} = 1.5 \text{ Vdc})$ $(V_{CE} = 140 \text{ Vdc}, V_{BE(off)} = 1.5 \text{ Vdc}, T_C = 150^{\circ}\text{C})$	I _{CEX}	- -	5.0 30	mAdc
Emitter Cutoff Current (V _{BE} = 7.0 Vdc, I _C = 0)	I _{EBO}	_	5.0	mAdc
ON CHARACTERISTICS (Note 3)	,			
DC Current Gain $ (I_C = 3.0 \text{ Adc, } V_{CE} = 4.0 \text{ Vdc)} $ $ (I_C = 10 \text{ Adc, } V_{CE} = 4.0 \text{ Vdc)} $	h _{FE}	20 7.5	70 -	-
Collector–Emitter Saturation Voltage (I _C = 10 Adc, I _B = 2.0 Adc)	V _{CE(sat)}	_	5.0	Vdc
Base–Emitter On Voltage ($I_C = 10 \text{ Adc}$, $V_{CE} = 4.0 \text{ Vdc}$)	V _{BE(on)}	-	5.7	Vdc
DYNAMIC CHARACTERISTICS				
Current–Gain – Bandwidth Product (Note 4) $(I_C = 2.0 \text{ Adc}, V_{CE} = 4.0 \text{ Vdc}, f_{test} = 40 \text{ kHz})$	f⊤	80	_	kHz
Small–Signal Current Gain ($I_C = 2.0$ Adc, $V_{CE} = 4.0$ Vdc, $f = 1.0$ kHz)	h _{fe}	12	72	-

^{3.} Pulse Test: Pulse Width = 300 μ s, Duty Cycle \leq 2.0%.

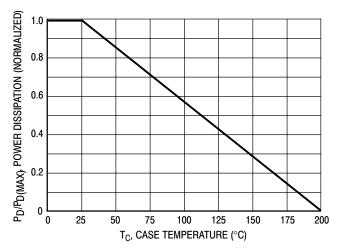


Figure 1. Power Derating

^{4.} $f_T = |h_{fe}| \bullet f_{test}$

ACTIVE REGION SAFE OPERATING AREA INFORMATION

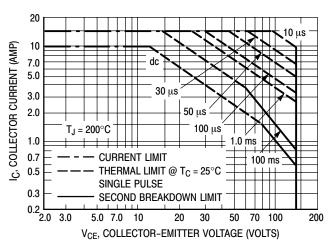


Figure 2. 2N3442

There are two limitations on the power–handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate $I_C - V_{CE}$ limits of the transistor that must be observed for reliable operation, i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 2 is based on $T_{J(pk)} = 200^{\circ}C$; T_C is variable depending on conditions. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

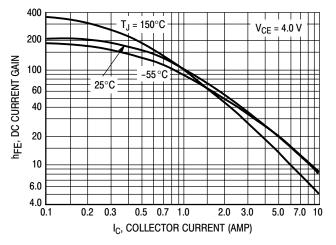


Figure 3. DC Current Gain

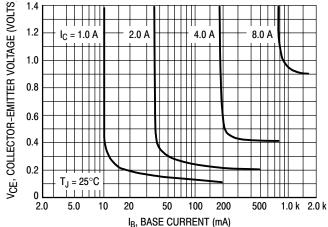


Figure 4. Collector-Saturation Region

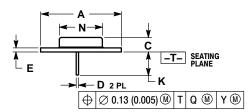


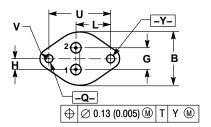
TO-204 (TO-3) **CASE 1-07 ISSUE Z**

DATE 05/18/1988



STYLE 1:





STYLE 2:

- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

STYLE 5:

 CONTROLLING DIMENSION: INCH.
 ALL RULES AND NOTES ASSOCIATED WITH REFERENCED TO-204AA OUTLINE SHALL APPLY.

	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	1.550 REF		39.37 REF	
В		1.050		26.67
С	0.250	0.335	6.35	8.51
D	0.038	0.043	0.97	1.09
Е	0.055	0.070	1.40	1.77
G	0.430 BSC		10.92 BSC	
Н	0.215 BSC		5.46	BSC
K	0.440	0.480	11.18	12.19
L	0.665 BSC		16.89	BSC
N		0.830		21.08
Q	0.151	0.165	3.84	4.19
U	1.187	1.187 BSC 30.1		BSC
٧	0.131	0.188	3.33	4.77

OTTLL I.	STILL Z.	STILL S.	STILL 4.	JIILL J.
PIN 1. BASE	PIN 1. BASE	PIN 1. GATE	PIN 1. GROUND	PIN 1. CATHODE
2. EMITTER	2. COLLECTOR	2. SOURCE	INPUT	EXTERNAL TRIP/DELAY
CASE: COLLECTOR	CASE: EMITTER	CASE: DRAIN	CASE: OUTPUT	CASE: ANODE
STYLE 6:	STYLE 7:	STYLE 8:	STYLE 9:	
PIN 1. GATE	PIN 1. ANODE	PIN 1. CATHODE #1	PIN 1. ANODE #1	
2. EMITTER	2. OPEN	CATHODE #2	ANODE #2	
CASE: COLLECTOR	CASE: CATHODE	CASE: ANODE	CASE: CATHODE	

STYLE 3:

STYLE 4:

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